

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	314229	438/\$.ccls. 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	8432	1 and mold	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	4427	2 and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	2707	3 and press\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L6	0	5 and template	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L5	17	4 and ((low near k) or low-k)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	L7	0	5 and redistribution	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	L8	39	Hofmann-James-J.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	BRS	L9	15	8 and mold	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	L10	0	9 and template	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	BRS	L11	15	9 and press\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	L12	46875	mold.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	BRS	L13	13449	12 and press\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	L14	739	13 and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	BRS	L16	211	14 and pattern	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	L17	0	16 and ((low near k) or low-k) near dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	BRS	L18	340177	mold	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	BRS	L19	3373	18 and template	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
19	BRS	L20	2436	19 and press\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
20	BRS	L21	1135	20 and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
21	BRS	L22	697	21 and pattern	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
22	BRS	L23	0	22 and ((low near k) or low-k) near dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
23	BRS	L25	0	24 and redistribution	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
24	BRS	L24	20	22 and (conductive or metal or bonding) near pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB